



# M74HC257

## QUAD 2 CHANNEL MULTIPLEXER (3-STATE)

- HIGH SPEED :  
 $t_{PD} = 11 \text{ ns (TYP.) at } V_{CC} = 6V$
- LOW POWER DISSIPATION:  
 $I_{CC} = 4\mu\text{A (MAX.) at } T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY:  
 $V_{NIH} = V_{NIL} = 28 \% V_{CC} \text{ (MIN.)}$
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 6\text{mA (MIN)}$
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \approx t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:  
 $V_{CC} \text{ (OPR)} = 2V \text{ to } 6V$
- PIN AND FUNCTION COMPATIBLE WITH  
 74 SERIES 257



### ORDER CODES

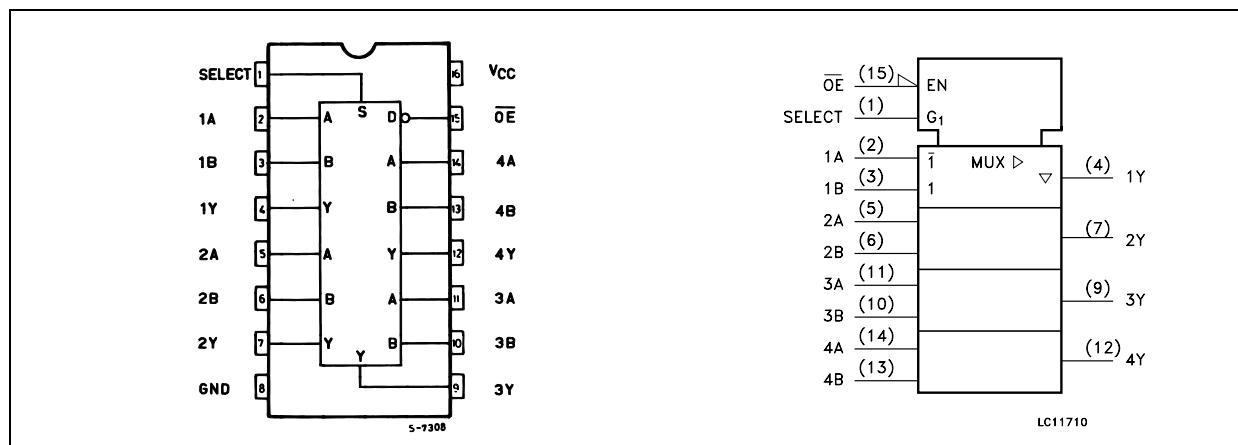
PACKAGE	TUBE	T & R
DIP	M74HC257B1R	
SOP	M74HC257M1R	M74HC257RM13TR
TSSOP		M74HC257TTR

### DESCRIPTION

The M74HC257 is an high speed CMOS QUAD 2 CHANNEL MULTIPLEXER (3-STATE) fabricated with silicon gate C<sup>2</sup>MOS technology. This IC is composed of an independent 2-channel multiplexer with common SELECT and ENABLE (OE) input. The M74HC257 is a non-inverting multiplexer.

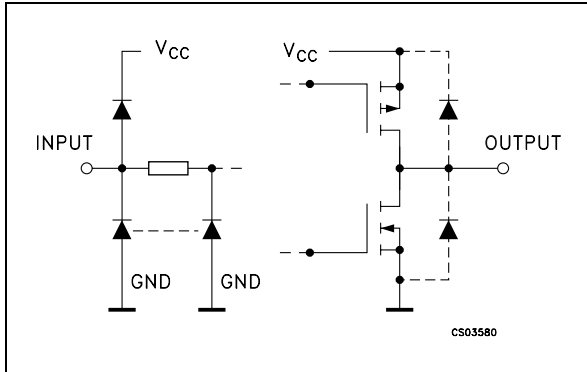
When the ENABLE input is held "High", outputs of the IC become in a High-Impedance state. If SELECT input is held low, "A" data is selected, when SELECT is high, "B" data is chosen. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



# M74HC257

## INPUT AND OUTPUT EQUIVALENT CIRCUIT



## PIN DESCRIPTION

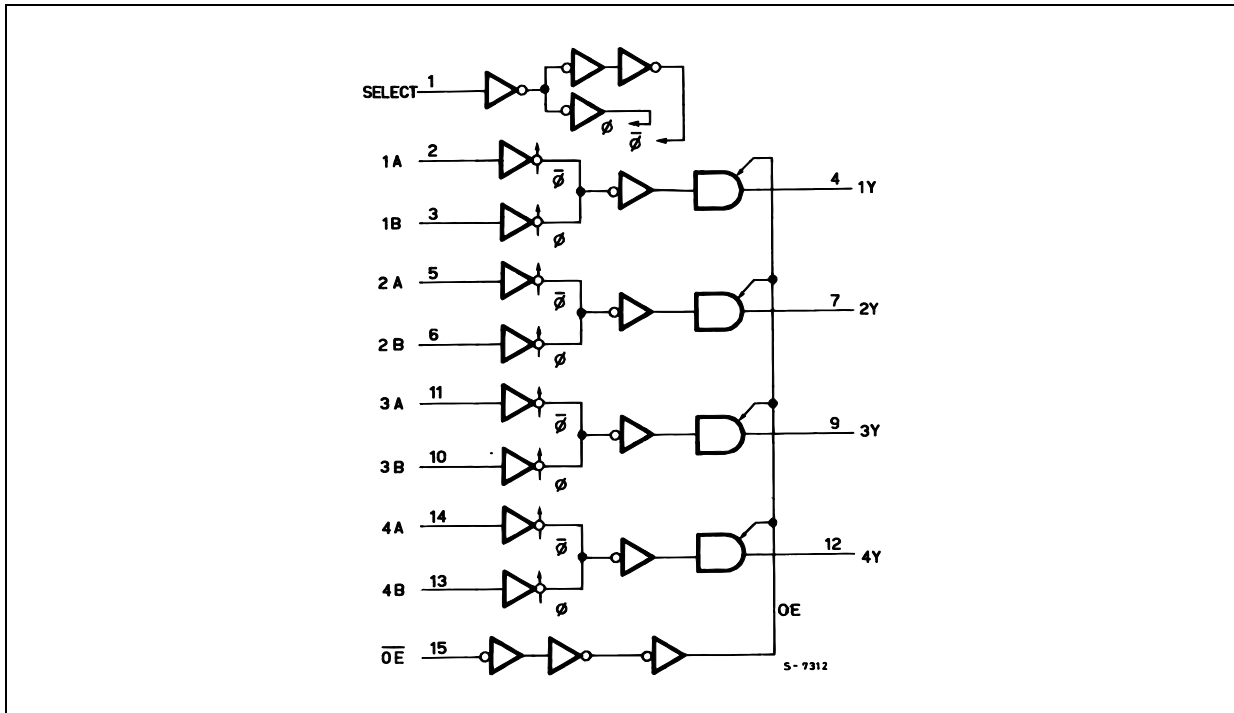
PIN No	SYMBOL	NAME AND FUNCTION
1	SELECT	Common Data Select Input
2, 5, 14, 11	1A to 4A	Data Input From Source A
3, 6, 13, 10	1B to 4B	Data Input From Source B
4, 7, 12, 9	1Y to 4Y	3 State Multiplexer Outputs
15	$\overline{OE}$	3 State Output Enable Inputs (Active Low)
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

## TRUTH TABLE

INPUTS				OUTPUT
$\overline{OE}$	SELECT	A	B	Y
H	X	X	X	Z
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

X : Don't Care  
Z : High Impedance

## LOGIC DIAGRAM



This logic diagram has not be used to estimate propagation delays

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply Voltage	-0.5 to +7	V
$V_I$	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
$V_O$	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	DC Input Diode Current	$\pm 20$	mA
$I_{OK}$	DC Output Diode Current	$\pm 20$	mA
$I_O$	DC Output Current	$\pm 35$	mA
$I_{CC}$ or $I_{GND}$	DC $V_{CC}$ or Ground Current	$\pm 70$	mA
$P_D$	Power Dissipation	500(*)	mW
$T_{stg}$	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit	
$V_{CC}$	Supply Voltage	2 to 6	V	
$V_I$	Input Voltage	0 to $V_{CC}$	V	
$V_O$	Output Voltage	0 to $V_{CC}$	V	
$T_{op}$	Operating Temperature	-55 to 125	°C	
$t_r, t_f$	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V <sub>IL</sub>	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
V <sub>OH</sub>	High Level Output Voltage	2.0	I <sub>O</sub> =-20 μA	1.9	2.0		1.9		1.9		V
		4.5	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I <sub>O</sub> =-20 μA	5.9	6.0		5.9		5.9		
		4.5	I <sub>O</sub> =-6.0 mA	4.18	4.31		4.13		4.10		
		6.0	I <sub>O</sub> =-7.8 mA	5.68	5.8		5.63		5.60		
V <sub>OL</sub>	Low Level Output Voltage	2.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		6.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		4.5	I <sub>O</sub> =6.0 mA		0.17	0.26		0.33		0.40	
		6.0	I <sub>O</sub> =7.8 mA		0.18	0.26		0.33		0.40	
I <sub>I</sub>	Input Leakage Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			± 0.1		± 1		± 1	μA
I <sub>OZ</sub>	High Impedance Output Leakage Current	6.0	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>O</sub> = V <sub>CC</sub> or GND			± 0.5		± 5		± 10	μA
I <sub>CC</sub>	Quiescent Supply Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			4		40		80	μA

AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6 \text{ ns}$ )

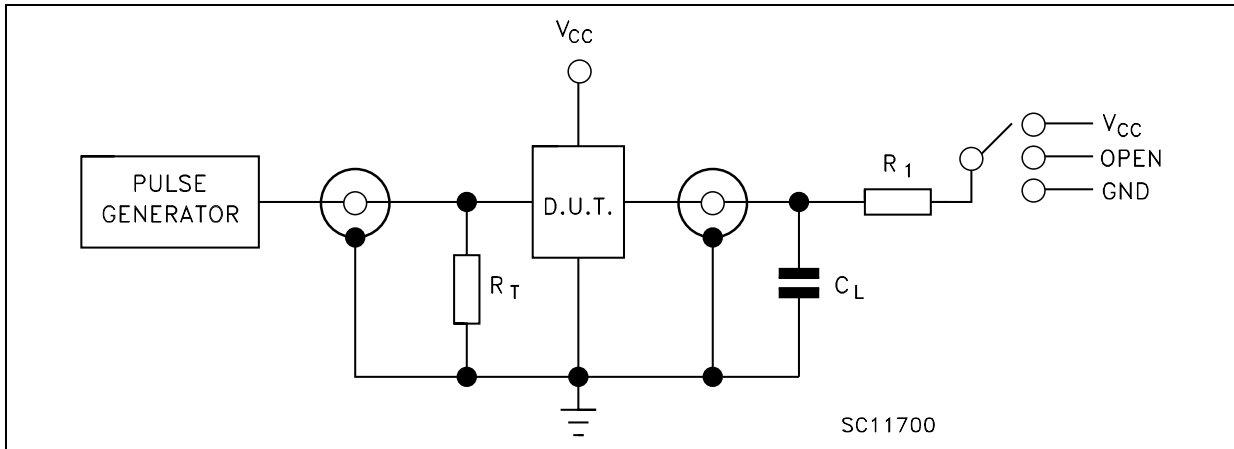
Symbol	Parameter	Test Condition			Value						Unit	
		$V_{CC}$ (V)			$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$t_{TLH}$ $t_{THL}$	Output Transition Time	2.0	50			25	60		75		90	ns
		4.5				7	12		15		19	
		6.0				6	10		13		15	
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time (A, B - Y)	2.0	50			45	100		125		150	ns
		4.5				13	20		25		30	
		6.0				11	17		21		26	
		2.0	150			62	140		175		210	ns
		4.5				18	28		35		42	
		6.0				15	24		30		36	
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time (SELECT - Y)	2.0	50			45	100		125		150	ns
		4.5				13	20		25		30	
		6.0				11	17		21		26	
		2.0	150			62	140		175		210	ns
		4.5				18	28		35		42	
		6.0				15	24		30		36	
$t_{PZL}$ $t_{PZH}$	High Impedance Output Enable Time	2.0	50	$R_L = 1 \text{ K}\Omega$		40	110		140		165	ns
		4.5				12	22		28		33	
		6.0				10	19		24		28	
		2.0	150	$R_L = 1 \text{ K}\Omega$		57	150		190		225	ns
		4.5				17	30		38		45	
		6.0				14	26		32		38	
$t_{PLZ}$ $t_{PHZ}$	High Impedance Output Disable Time	2.0	50	$R_L = 1 \text{ K}\Omega$		28	140		175		210	ns
		4.5				14	28		35		42	
		6.0				13	24		30		36	

## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition			Value						Unit	
		$V_{CC}$ (V)			$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$C_{IN}$	Input Capacitance					5	10		10		10	pF
$C_{OUT}$	Output Capacitance					10						pF
$C_{PD}$	Power Dissipation Capacitance (note 1)					47						pF

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(oper)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$  (per Channel)

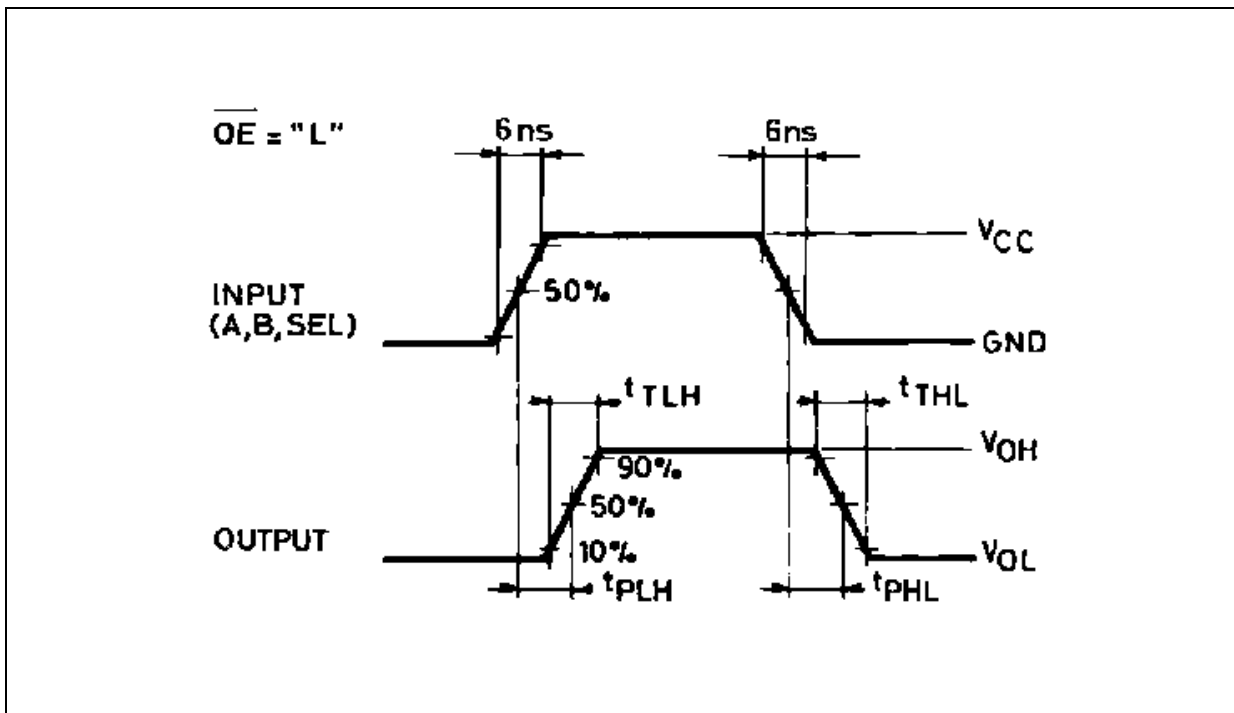
TEST CIRCUIT



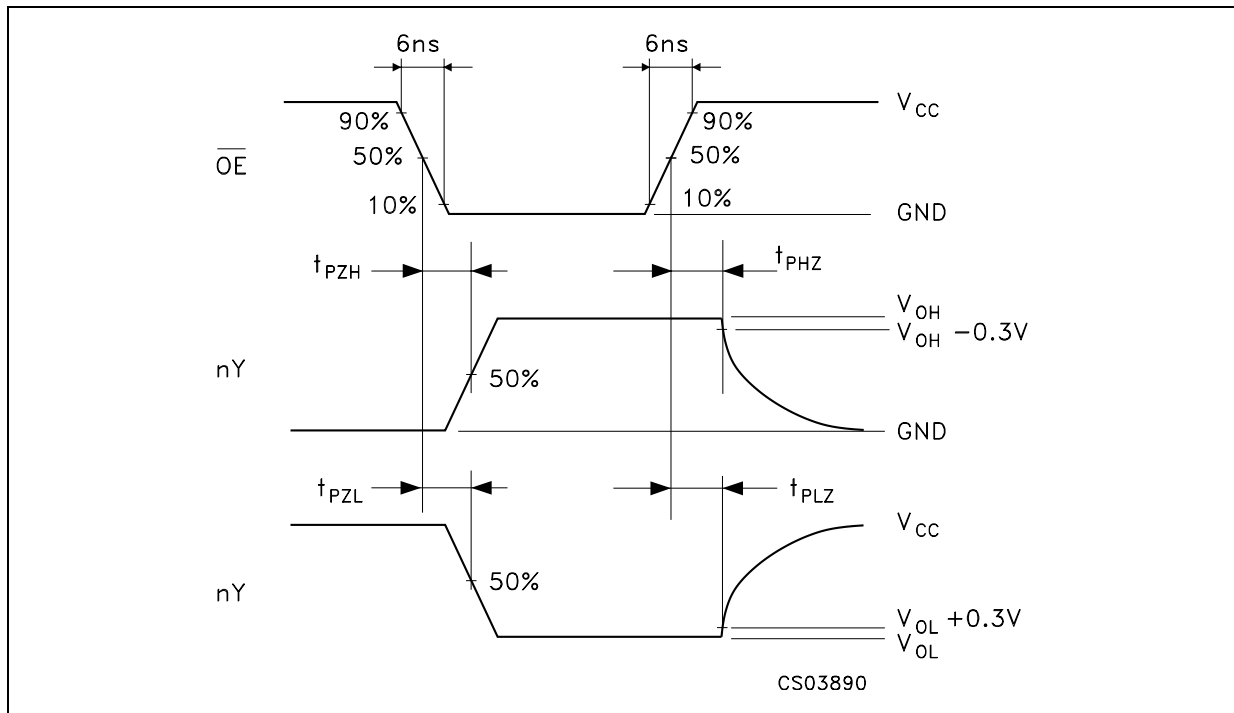
TEST	SWITCH
$t_{PLH}, t_{PHL}$	Open
$t_{PZL}, t_{PLZ}$	$V_{CC}$
$t_{PZH}, t_{PHZ}$	GND

$C_L = 50\text{pF}/150\text{pF}$  or equivalent (includes jig and probe capacitance)  
 $R_1 = 1\text{K}\Omega$  or equivalent  
 $R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

WAVEFORM 1: PROPAGATION DELAY TIME ( $f=1\text{MHz}$ ; 50% duty cycle)

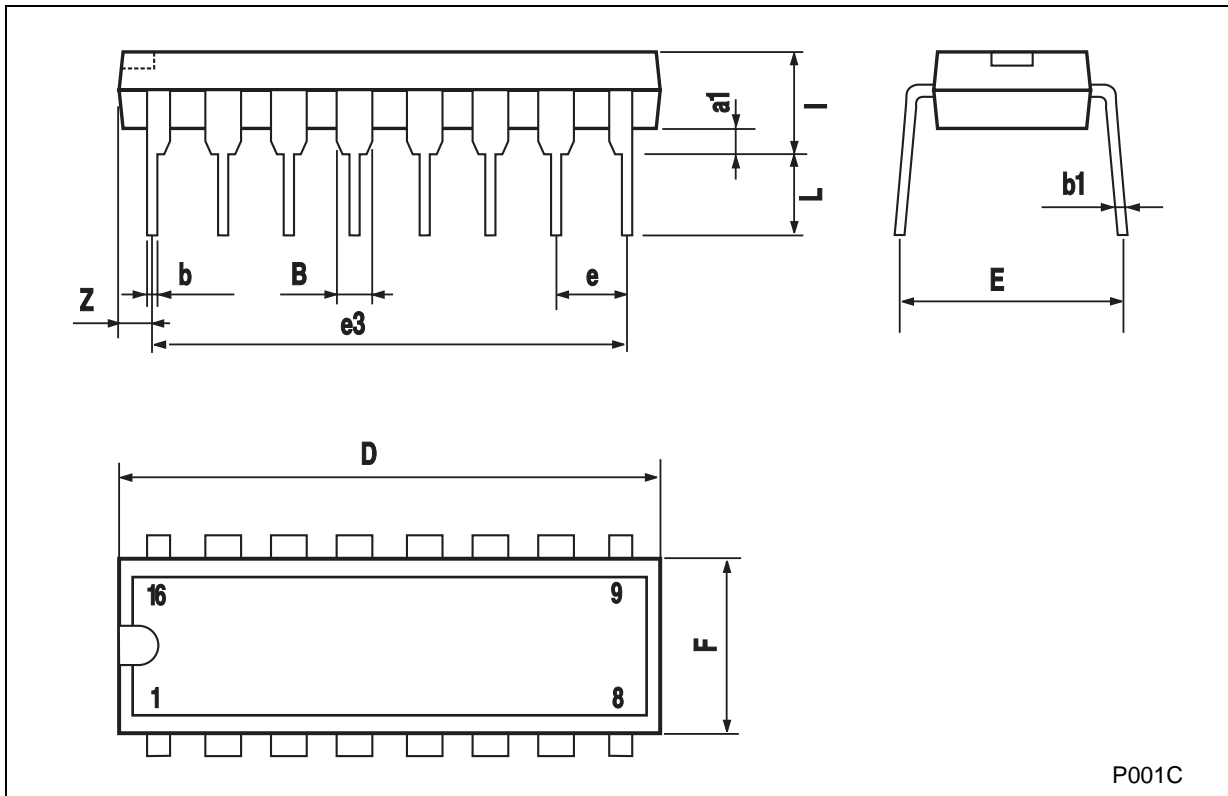


WAVEFORM 2 : OUTPUT ENABLE AND DISABLE TIME (f=1MHz; 50% duty cycle)



**Plastic DIP-16 (0.25) MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050





## SO-16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



**TSSOP16 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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